

Description

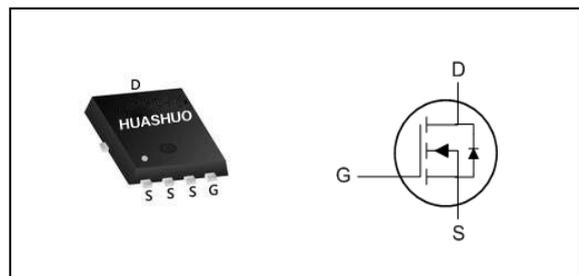
The HSBA6074 is the high cell density SGT N-ch MOSFETs, which provide excellent R_{DS(on)} and gate charge for most of the synchronous buck converter applications.

The HSBA6074 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- Motor Control
- 100% EAS Guaranteed
- DC/DC Converter.
- Excellent CdV/dt effect decline
- Synchronous rectifier applications.

Product Summary

V _{DS}	60	V
R _{DS(ON),typ}	1.7	mΩ
I _D	100	A

PRPAK5X6 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	60	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current ^{1,6}	100	A
I _D @T _C =100°C	Continuous Drain Current ^{1,6}	66	A
I _{DM}	Pulsed Drain Current ²	400	A
EAS	Single Pulse Avalanche Energy ³	306	mJ
I _{AS}	Avalanche Current	35	A
P _D @T _C =25°C	Total Power Dissipation ⁴	83	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient ¹	---	55	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	1.1	°C/W

N-Ch 60V Fast Switching MOSFETs
Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=20A$	---	1.7	2.1	$m\Omega$
		$V_{GS}=4.5V, I_D=20A$	---	2.3	3.2	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	---	2.3	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=52V, V_{GS}=0V, T_J=25^\circ C$	---	---	1	μA
		$V_{DS}=52V, V_{GS}=0V, T_J=55^\circ C$	---	---	5	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=20A$	---	60	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	---	1.6	---	Ω
Q_g	Total Gate Charge (10V)	$V_{DS}=30V, V_{GS}=10V, I_D=20A$	---	102	---	nC
Q_{gs}	Gate-Source Charge		---	16	---	
Q_{gd}	Gate-Drain Charge		---	28	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=30V, V_{GS}=10V, R_G=3\Omega, I_D=20A$	---	15	---	ns
T_r	Rise Time		---	12	---	
$T_{d(off)}$	Turn-Off Delay Time		---	60	---	
T_f	Fall Time		---	19	---	
C_{iss}	Input Capacitance	$V_{DS}=30V, V_{GS}=0V, f=1MHz$	---	5480	---	pF
C_{oss}	Output Capacitance		---	1822	---	
C_{rss}	Reverse Transfer Capacitance		---	88	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	100	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ C$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=20A, di/dt=100A/\mu s, T_J=25^\circ C$	---	50	---	nS
Q_{rr}	Reverse Recovery Charge		---	72	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=50V, V_{GS}=10V, L=0.5mH, I_{AS}=35A$
- 4.The power dissipation is limited by 150 $^\circ C$ junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.
- 6.The maximum current rating is package limited.

Typical Characteristics

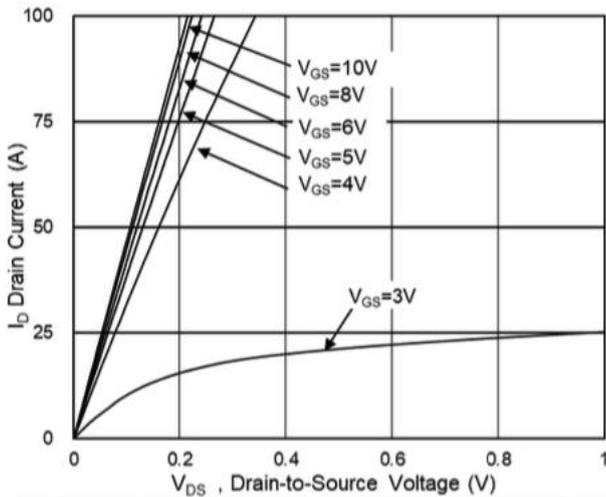


Fig.1 Typical Output Characteristics

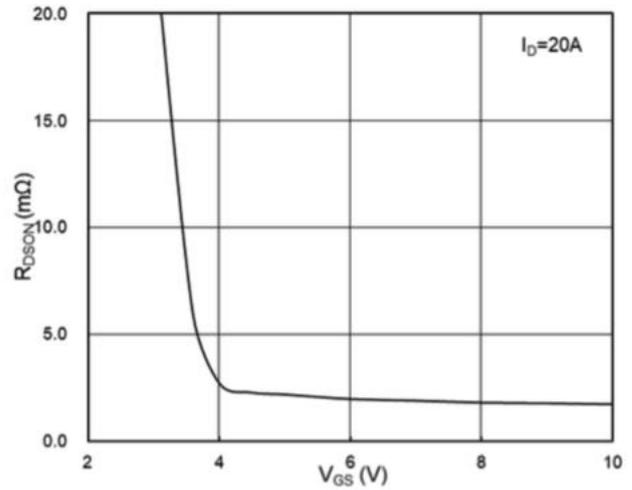


Fig.2 On-Resistance vs G-S Voltage

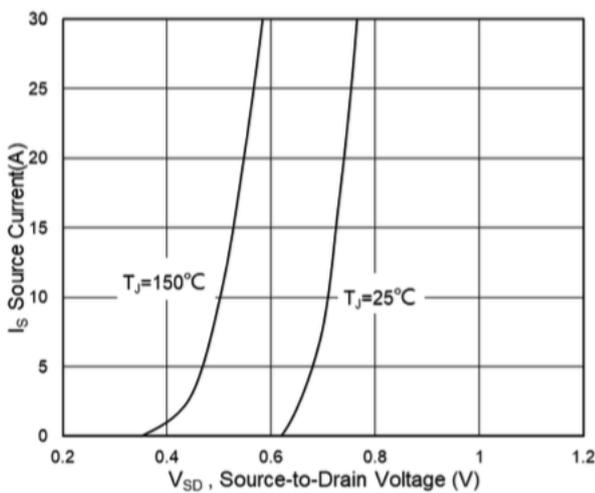


Fig.3 Diode Forward Voltage vs. Current

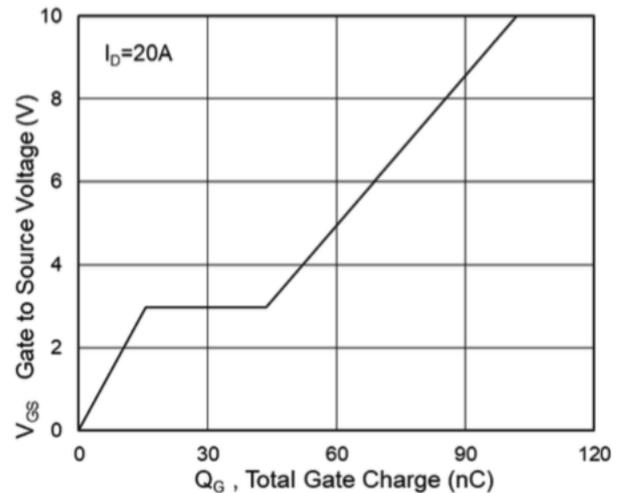


Fig.4 Gate-Charge Characteristics

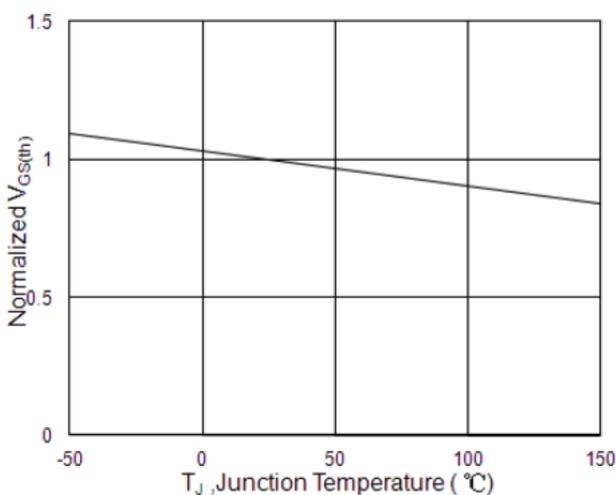


Fig.5 Normalized $V_{GS(th)}$ vs T_J

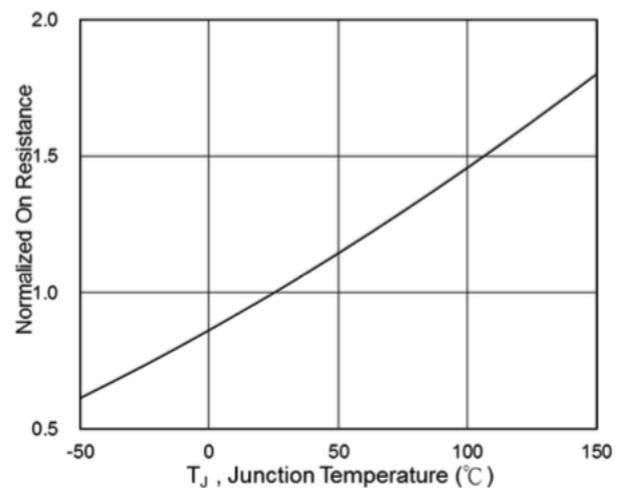


Fig.6 Normalized $R_{DS(on)}$ vs T_J

N-Ch 60V Fast Switching MOSFETs

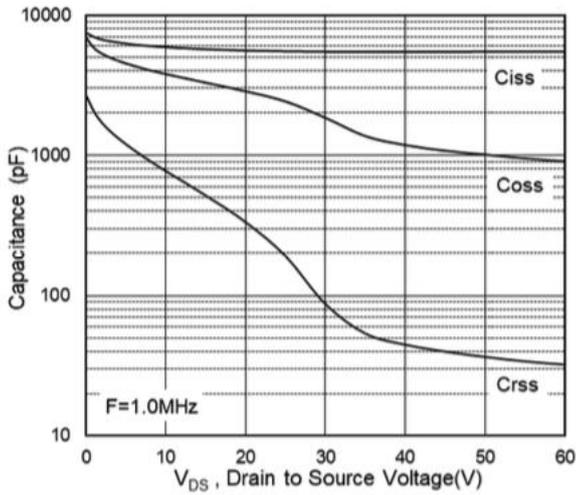


Fig.7 Capacitance

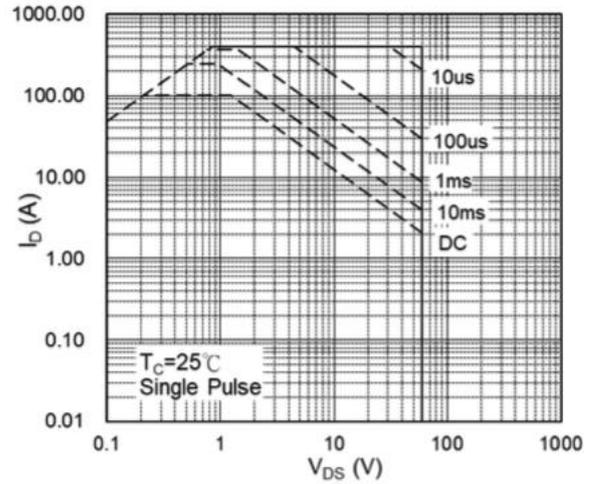


Fig.8 Safe Operating Area

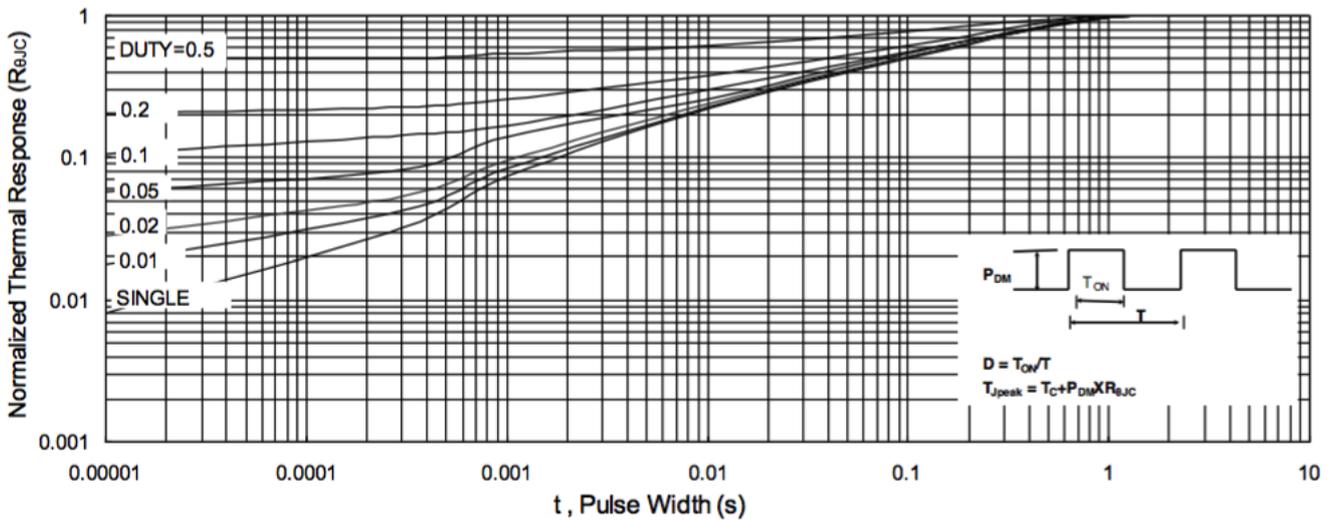


Fig.9 Normalized Maximum Transient Thermal Impedance

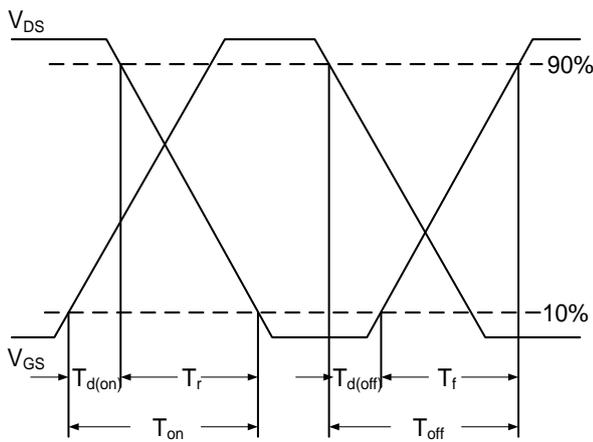


Fig.10 Switching Time Waveform

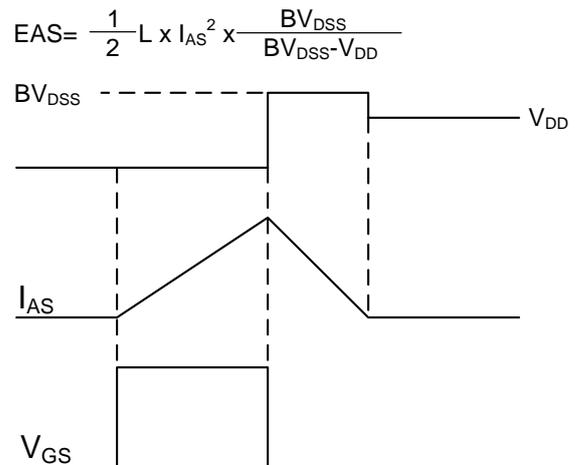
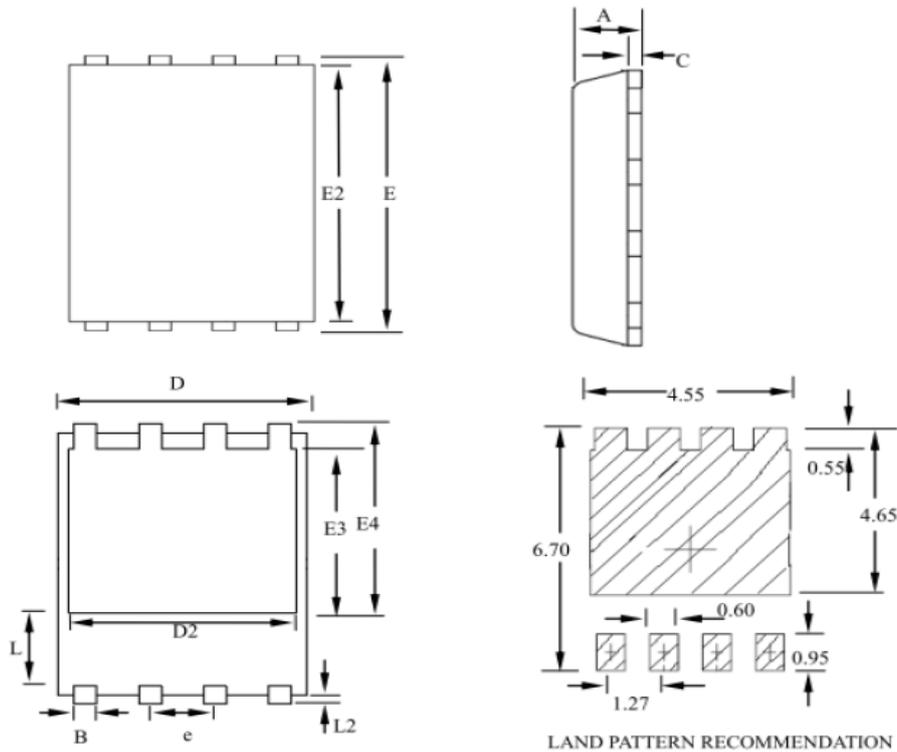


Fig.11 Unclamped Inductive Switching

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

Ordering Information

Part Number	Package code	Packaging
HSBA6074	PRPAK5*6	3000/Tape&Reel



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	--	1.20	0.031	--	0.047
B	0.30	--	0.51	0.012	--	0.020
C	0.15	--	0.35	0.006	--	0.014
D	4.80	--	5.30	0.189	--	0.209
D2	3.61	--	4.35	0.142	--	0.171
E	5.90	--	6.35	0.232	--	0.250
E2	5.42	--	5.90	0.213	--	0.232
E3	3.23	--	3.90	0.127	--	0.154
E4	3.69	--	4.55	0.145	--	0.179
L	0.61	--	1.80	0.024	--	0.071
L2	0.05	--	0.36	0.002	--	0.014
e	--	1.27	--	--	0.050	--

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